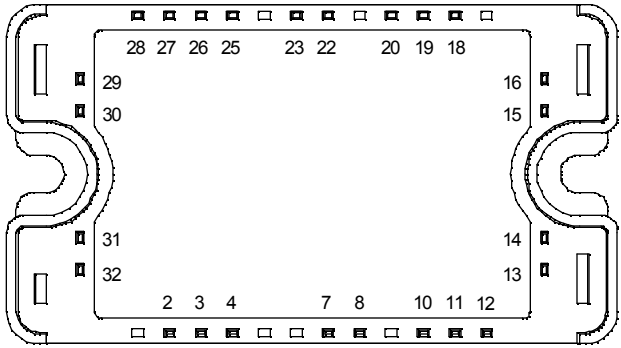
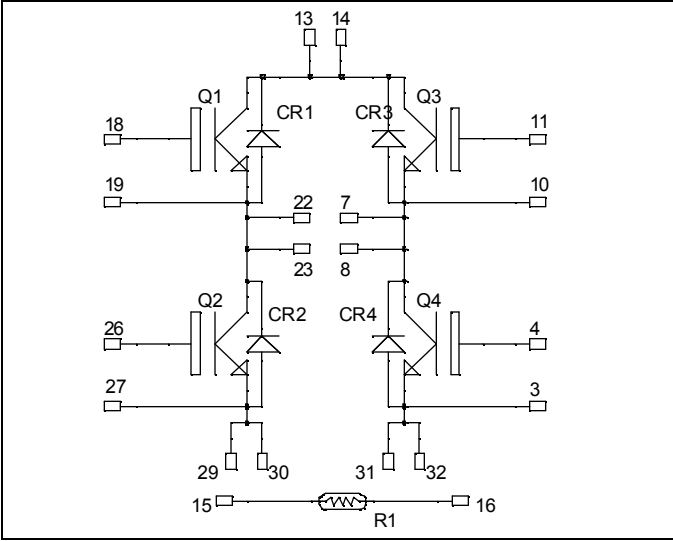


**Full - Bridge
Trench IGBT® Power Module**

**$V_{CES} = 1700V$
 $I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	45
		$T_c = 80^\circ C$	30
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	70
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	210
RBSOA	Reverse Bias Safe Operation Area	$T_j = 125^\circ C$	120A@1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 1.5\text{mA}$	1700			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1700\text{V}$			3	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$		2.0	2.4	V
		$I_C = 30\text{A}$	$T_j = 25^\circ\text{C}$			
				2.4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{mA}$	5.2	5.8	6.4	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$		2500		pF
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		90		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 30\text{A}$ $R_G = 18\Omega$		100		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 30\text{A}$ $R_G = 18\Omega$		100		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			750		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy ①			18		mJ
E_{off}	Turn-off Switching Energy ②			19		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
V_F	Diode Forward Voltage	$I_F = 50\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.8	2.2	V
			$T_j = 125^\circ\text{C}$	1.9		
E_r	Reverse Recovery Energy	$I_F = 50\text{A}$ $V_R = 900\text{V}$ $di/dt = 990\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	8		mJ
			$T_j = 125^\circ\text{C}$	15		
Q_{rr}	Reverse Recovery Charge	$I_F = 50\text{A}$ $V_R = 900\text{V}$ $di/dt = 990\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	18		μC
			$T_j = 125^\circ\text{C}$	29		

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		$\text{k}\Omega$
$B_{25/85}$	$T_{25} = 298.16\text{K}$		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

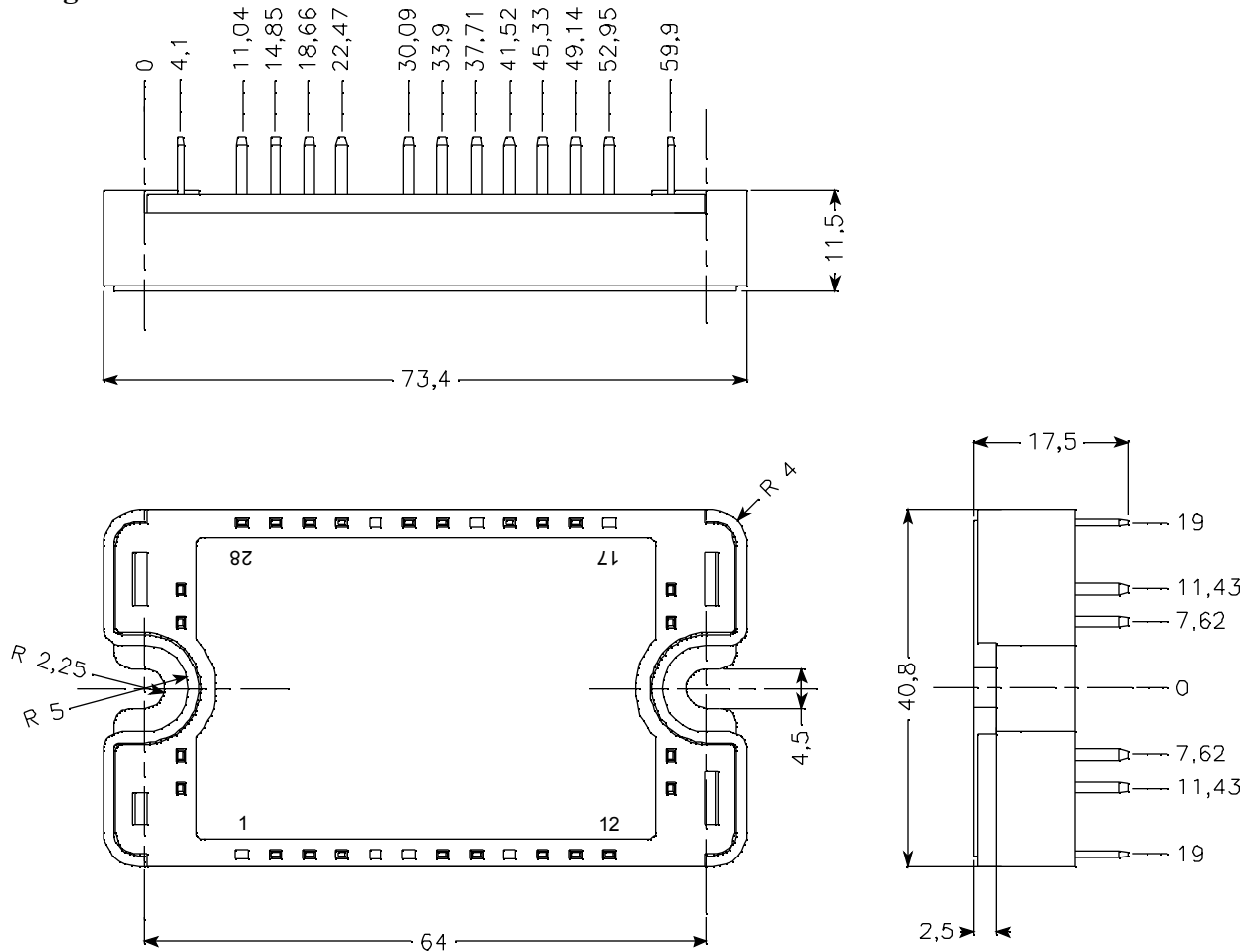
T: Thermistor temperature
 R_T : Thermistor value at T

Thermal and package characteristics

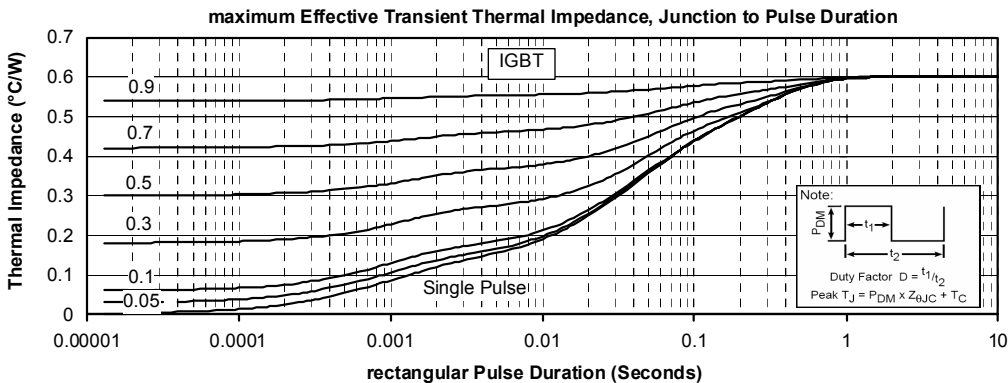
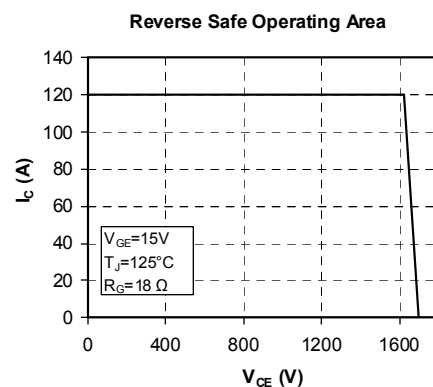
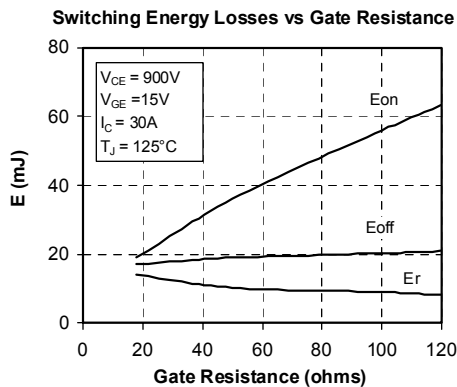
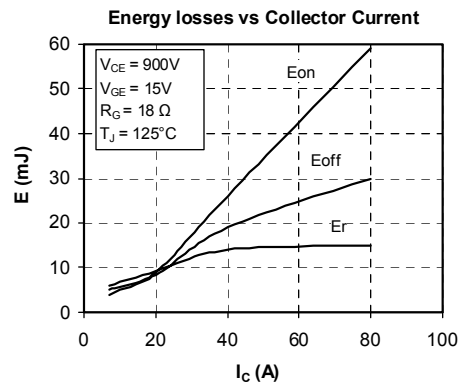
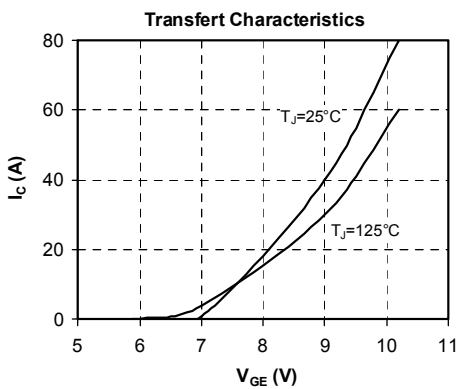
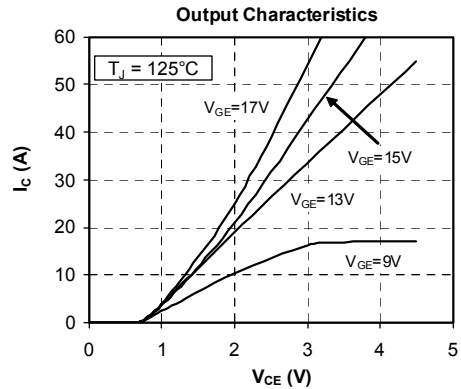
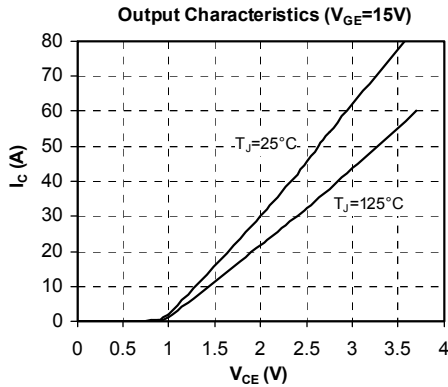
Symbol Characteristic

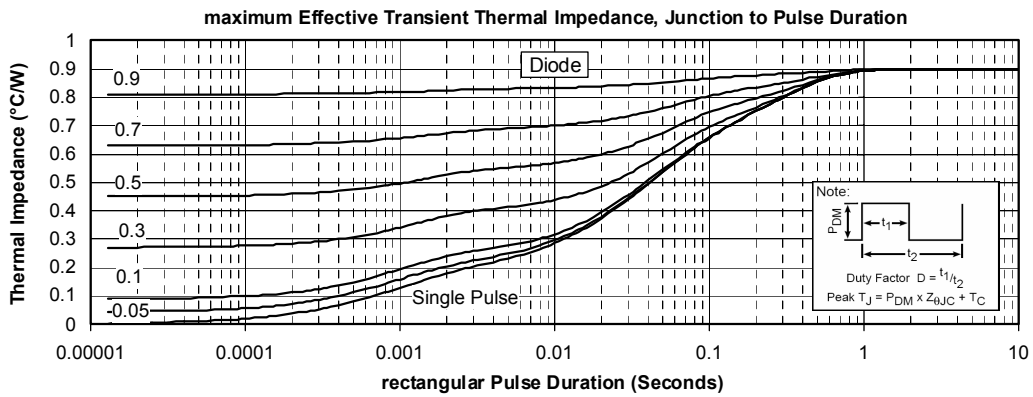
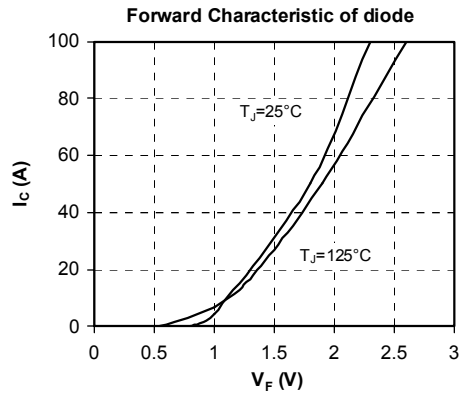
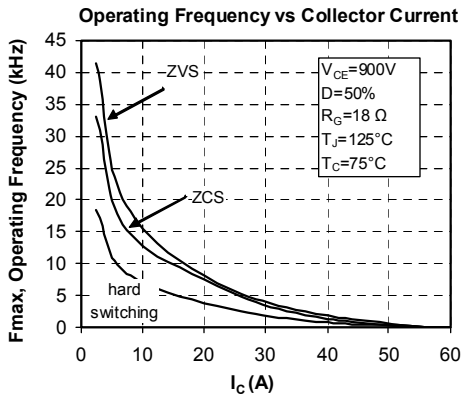
			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R _{thJC}	Junction to Case	IGBT			0.6	°C/W
		Diode			0.9	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz		3500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M4		4.7	N.m
Wt	Package Weight				110	g

Package outline



Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.